

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|--------------------|---------------------------------|---|--|-----|-----|-----|------|--|
| V_{RRM} | repetitive peak reverse voltage | | | - | - | 600 | V | |
| I _{F(AV)} | average forward current | δ = 0.5; square-wave pulse; Fig. 1; Fig. 2 | | - | - | 15 | Α | |
| Static characte | eristics | | | | | | | |
| V _F | forward voltage | I _F = 15 A; T _j = 150 °C; <u>Fig. 5</u> | | - | 1.4 | 2 | V | |
| Dynamic chara | Dynamic characteristics | | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6 | | - | 13 | 18 | ns | |





5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--------------------|----------------|
| 1 | K | cathode | mb | K — A |
| 2 | Α | anode | | 001aaa020 |
| mb | n.c. | mounting base; isolated | TO-220F (SOD113A) | |

6. Ordering information

Table 3. Ordering information

| Table of Cracing | | | | | | |
|------------------|---------|--|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| BYC15X-600P | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack" | SOD113A | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BYC15X-600P | BYC15X-600P |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|---------------------------------|---|-----|-----|------|
| V _{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V _{RWM} | crest working reverse voltage | | - | 600 | V |
| V _R | reverse voltage | DC | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5; square-wave pulse; Fig. 1; Fig. 2 | - | 15 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5; t_p = 25 μ s; square-wave pulse | - | 30 | Α |

BYC15X-600P

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NXP Semiconductors BYC15X-600P

Hyperfast power diode

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------------------|---|-----|-----|------|
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 3</u> | - | 180 | Α |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 3</u> | - | 200 | Α |
| T _{stg} | storage temperature | | -65 | 175 | °C |
| T _j | junction temperature | | - | 175 | °C |

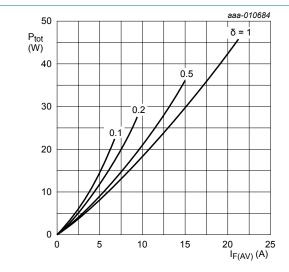


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$
 $V_{O} = 1.578 \text{ V}; R_{S} = 0.027 \Omega$

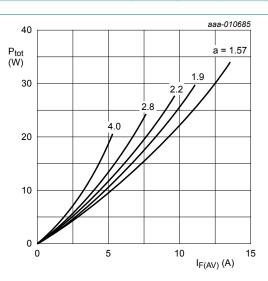


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 V_{\odot} = 1.578 V; R_{S} = 0.027 Ω

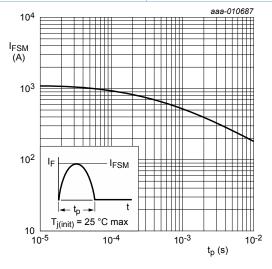
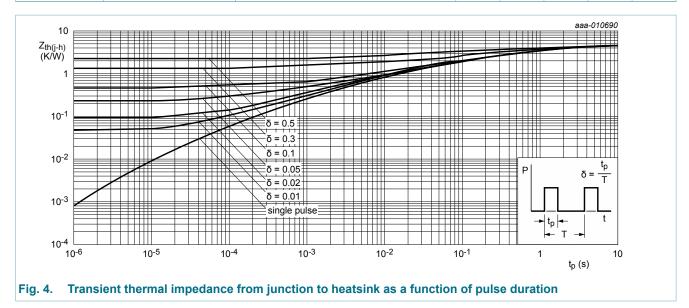


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--------------------------------|-----|-----|-----|------|
| R _{th(j-h)} | thermal resistance from junction to heatsink | with heatsink compound; Fig. 4 | - | - | 4.5 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 55 | - | K/W |



10. Isolation characteristics

Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|-----------------------|---|-----|-----|------|------|
| V _{isol(RMS)} | RMS isolation voltage | 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C _{isol} | isolation capacitance | f = 1 MHz; from cathode to external heatsink | - | 10 | - | pF |

11. Characteristics

Table 8. Characteristics

| Tubio o. Ona | i dotoriotioo | | | | | | |
|---|-----------------|--|--|-----|-----------------|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| Static characteristics | | | | | | | |
| V _F | forward voltage | I _F = 15 A; T _j = 25 °C; <u>Fig. 5</u> | | - | 2.7 | 3.2 | V |
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NXP Semiconductors BYC15X-600P

Hyperfast power diode

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|--|-----|-----|-----|------|
| | | I _F = 15 A; T _j = 150 °C; <u>Fig. 5</u> | - | 1.4 | 2 | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | - | - | 10 | μΑ |
| | | V _R = 600 V; T _j = 150 °C | - | - | 1 | mA |
| Dynamic cl | haracteristics | | | | | |
| Q _r | recovered charge | I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; <u>Fig. 6</u> | - | 30 | - | nC |
| | | I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 125 °C; <u>Fig. 6</u> | - | 115 | - | nC |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$ | - | 13 | 18 | ns |
| | | $I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ μ s; $T_j = 25 \text{ °C}; Fig. 6$ | - | 22 | - | ns |
| | | I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; Fig. 6 | - | 28 | - | ns |
| | | I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 125 °C; <u>Fig. 6</u> | - | 39 | - | ns |
| I _{RM} | peak reverse recovery current | I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; <u>Fig. 6</u> | - | 2.1 | - | A |
| | | $I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 6$ | - | 5.8 | - | A |

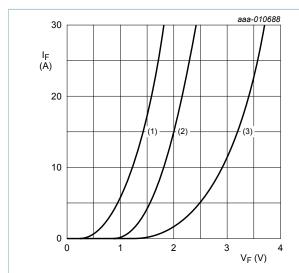


Fig. 5. Forward current as a function of forward voltage

(1) T_j = 150 °C; typical values; (2) T_j = 150 °C; maximum values; (3) T_j = 25 °C; maximum values; V_O = 1.578 V; R_S = 0.027 Ω

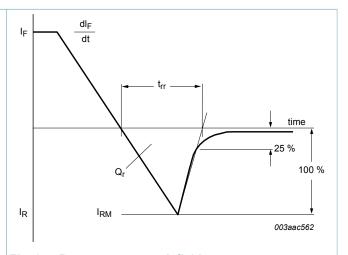
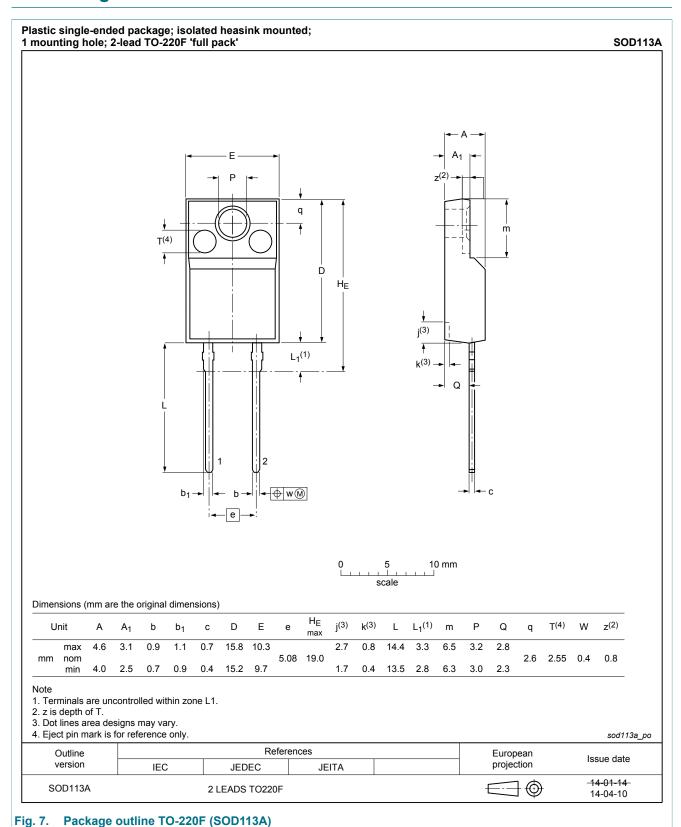


Fig. 6. Reverse recovery definitions; ramp recovery

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12. Package outline

BYC15X-600P



13. Legal information

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